

INCHANGE Semiconductor

isc Product Specification

isc Silicon NPN Darlington Power Transistor

BU807FI

DESCRIPTION

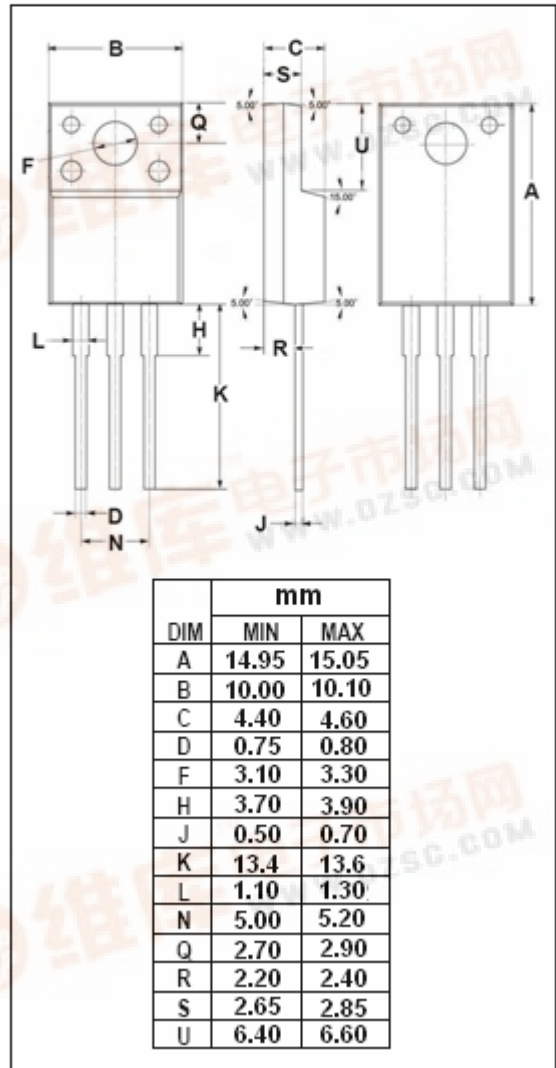
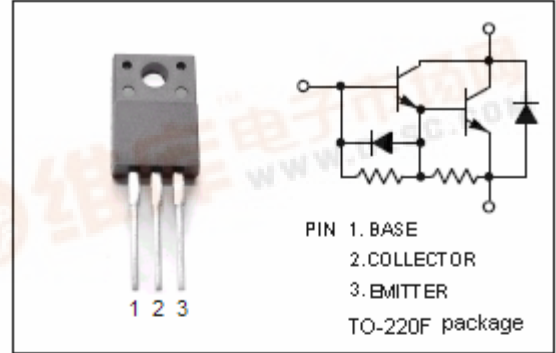
- High Voltage:  $V_{CBO} = 330V(\text{Min})$
- Low Saturation Voltage-  
:  $V_{CE(\text{sat})} = 1.5V(\text{Max}) @ I_C = 5A$

APPLICATIONS

- Designed for use in horizontal deflection circuits in TV's and CRT's.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	330	V
$V_{CEV}$	Collector-Emitter Voltage	330	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	8	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current	2	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ C$	30	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Darlington Power Transistor****BU807FI****ELECTRICAL CHARACTERISTICS** $T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 100\text{mA}; I_B= 0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 5\text{A}; I_B= 50\text{mA}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 5\text{A}; I_B= 50\text{mA}$			2.4	V
$I_{CES}$	Collector Cutoff Current	$V_{CE}= 330\text{V}; V_{BE}= 0$			0.1	mA
$I_{CEV}$	Collector Cutoff Current	$V_{CE}= 330\text{V}; V_{BE(off)}= 6\text{V}$			0.1	mA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}= 6\text{V}; I_C= 0$			3.0	mA
$V_{ECF}$	C-E Diode Forward Voltage	$I_F= 4\text{A}$			2.0	V